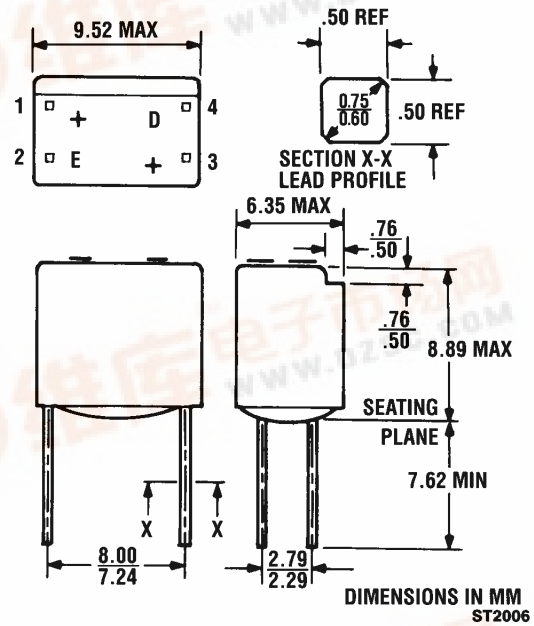
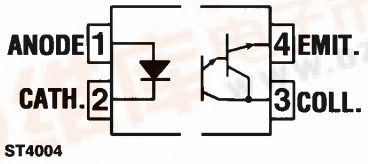
OPTOELECTRONICS

H24B1 H24B2

PACKAGE DIMENSIONS





Equivalent Circuit

DESCRIPTION

The H24B series consists of a gallium arsenide infrared emitting diode coupled with a silicon phototransistor. The devices are housed in a low-cost plastic package with lead spacing compatible with a dual in-line package.

FEATURES

- 4-pin configuration
- Small package size and low cost
- UL recognized-file E51868
- High current transfer ratio

ABSOLUTE MAXIMUM RATINGS

TOTAL PACKAGE

Storage temperature . . . . . −55°C to 85°C
Operating temperature . . . . . −55°C to 85°C
Lead solder temperature . . . . . 260°C for 5 sec

INPUT DIODE

Power dissipation (25°C ambient) . . . . . 100 mW
Derate linearly (above 25°C) . . . . . 1.67 mW/°C
Continuous forward current . . . . . 60 mA
Peak forward current (1 μs pulse, 300pps) . . . . . 3 A
Reverse voltage . . . . . 4 V

DETECTOR

Power dissipation (at 25°C ambient) . . . . . 150 mW
Derate linearly (above 25°C ambient) . . . . 2.5 mW/°C
V_{CEO} . . . . . 30 V
V_{ECO} . . . . . 7 V
Continuous forward current . . . . . 100 mA